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FDA16N50_F109 N-Channel UniFETTM MOSFET 500V, 16.5 A, 380 mΩ

Features

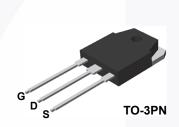
- $R_{DS(on)}$ = 380 m Ω (Max.) @ V_{GS} = 10, I_D = 8.3 A
- Low Gate Charge (Typ. 32 nC)
- Low C_{rss} (Typ. 20 pF)
- 100% Avalanche Tested

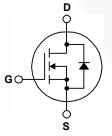
Applications

- PDP TV
- Uninterruptible Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

| Symbol | Parameter | | | FDA16N50_F109 | Unit | |
|----------------------------------|---|---|----------|---------------|-----------|--|
| V _{DSS} | Drain-Source Voltag | e | | 500 | V | |
| ID | Drain Current | - Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$) | | 16.5 9.9 | A A | |
| I _{DM} | Drain Current | - Pulsed | (Note 1) | 66 | А | |
| V _{GSS} | Gate-Source voltage | | | ±30 | V | |
| E _{AS} | Single Pulsed Avalanche Energy | | (Note 2) | 780 | mJ | |
| I _{AR} | Avalanche Current | | (Note 1) | 16.5 | A | |
| E _{AR} | Repetitive Avalanche Energy | | (Note 1) | 20.5 | mJ | |
| dv/dt | Peak Diode Recovery dv/dt | | (Note 3) | 4.5 | V/ns | |
| P _D | Power Dissipation | (T _C = 25°C) - Derate above 25°C | | 205 2.1 | W W/°C | |
| T _{J,} T _{STG} | Operating and Storage Temperature Range | | | -55 to +150 | °C | |
| Τ _L | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | | | 300 | °C | |

Thermal Characteristics

| Symbol | Parameter | FDA16N50_F109 | Unit | |
|-----------------|---|---------------|------|--|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max. | 0.6 | °C/W | |
| R_{\thetaJA} | Thermal Resistance, Junction-to-Ambient, Max. | 40 | | |

| Device i | annig | Device | 1 aur | aye | ILEEI SIZE | ιαρ | e Wiutii Quali | | lity | |
|---------------------------------------|---|-----------------------------|------------|---|--------------------------|----------|----------------|------|----------|----------|
| FDA16N50 | | FDA16N50_F109 | TO-3PN | | Tube | | N/A | | 30 units | |
| Electric | al Cha | racteristics ⊤ _c | = 25°C unl | ess otherw | vise noted. | | | | | |
| Symbol | | Parameter | | | Conditions | | Min. | Тур. | Max | Unit |
| Off Charac | teristics | | | | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | | | V _{GS} = 0V, | I _D = 250μA | | 500 | | | V |
| ΔBV_{DSS} / ΔT_{J} | Breakdown Voltage Temperature Coefficient | | | $I_D = 250\mu A$, Referenced to $25^{\circ}C$ | | | | 0.5 | | V/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | | | $V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_{C} = 125^{\circ}C$ | | | | | 1 10 | μΑ μΑ |
| I _{GSSF} | Gate-Bod | ly Leakage Current, F | orward | V _{GS} = 30V | , V _{DS} = 0V | | | - | 100 | nA |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | | Reverse | $V_{GS} = -30V, V_{DS} = 0V$ | | | | | -100 | nA |
| On Charact | teristics | | | | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | | | V _{DS} = V _{GS} | , I _D = 250μA | | 3.0 | | 5.0 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | | | V _{GS} = 10V, I _D = 8.3A | | | | 0.31 | 0.38 | Ω |
| 9 _{FS} | Forward Transconductance | | | V _{DS} = 40V, I _D = 8.3A | | | 23 | | S | |
| Dynamic C | haracteris | stics | | | | | | | | |
| C _{iss} | Input Cap | t Capacitance | | V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz | | | 1495 | 1945 | pF | |
| C _{oss} | Output Capacitance Reverse Transfer Capacitance | | | | | | 235 | 310 | pF | |
| C _{rss} | | | | | | | 20 | 30 | pF | |
| Switching | Character | istics | | | | | | | | |
| t _{d(on)} | Turn-On Delay Time | | | V _{DD} = 250V, I _D = 16A | | | 40 | 90 | ns | |
| t _r | Turn-On I | Rise Time | | $R_{G} = 25\Omega$ | | | 150 | 310 | ns | |
| t _{d(off)} | Turn-Off I | Delay Time | | | | | | 65 | 140 | ns |
| t _f | Turn-Off I | Fall Time | | (Note 4 | | (Note 4) | | 80 | 170 | ns |
| Qg | Total Gate | e Charge | | V _{DS} = 400V, I _D = 16A V _{GS} = 10V (Note 4) | | | 32 | 45 | nC | |
| Q _{gs} | Gate-Sou | Irce Charge | | | | | 8.5 | | nC | |
| Q _{gd} | Gate-Dra | in Charge | | | | | 14 | | nC | |
| Drain-Sour | ce Diode (| Characteristics and | Maximum | Ratings | | | | | | |
| I _S | Maximum Continuous Drain-Source Diode Forward Current | | | | | | | 9.2 | А | |
| I _{SM} | Maximum Pulsed Drain-Source Diode Fo | | | orward Current | | | | | 37 | А |
| V _{SD} | Drain-Sou | urce Diode Forward V | oltage | V _{GS} = 0V, | I _S = 16.5A | | | | 1.4 | V |
| t _{rr} | Reverse | Recovery Time | | V _{GS} = 0V, | | | | 490 | - | ns |
| Q _{rr} | Reverse | Recovery Charge | | dI _F /dt =100A/μs | | | 5.0 | | μC | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity | |
|----------------|---------------|---------|-----------|------------|----------|--|
| FDA16N50 | FDA16N50_F109 | TO-3PN | Tube | N/A | 30 units | |

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. L = 5.1mH, I_{AS} = 16.5A, V_DD = 50V, R_G = 25 Ω , Starting T_J = 25°C

3. I_{SD} \leq 16.5A, di/dt \leq 200A/µs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C

4. Essentially Independent of Operating Temperature Typical Characteristics

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Notes : 1. V_{DS} = 40V

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Notes : 1. V_{GS} = 0V

2.0 2.2 2.4

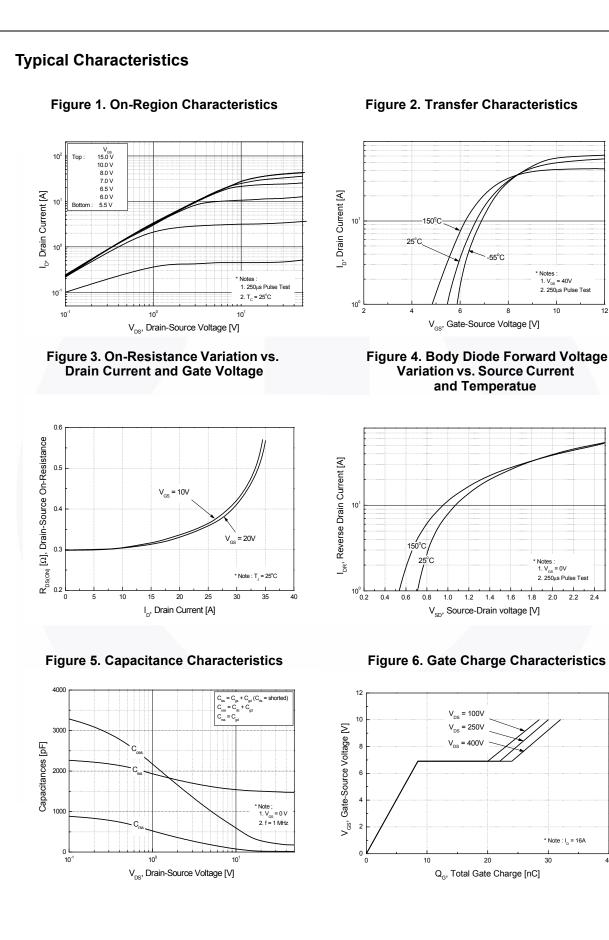
2. 250µs Pulse Tes

* Note : I_p = 16A

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2. 250µs Pulse Test

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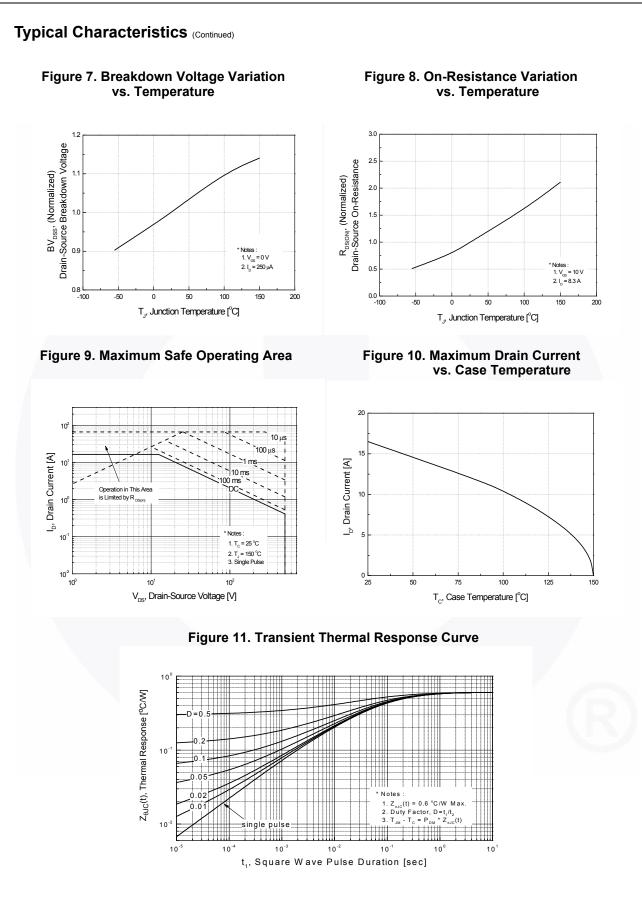


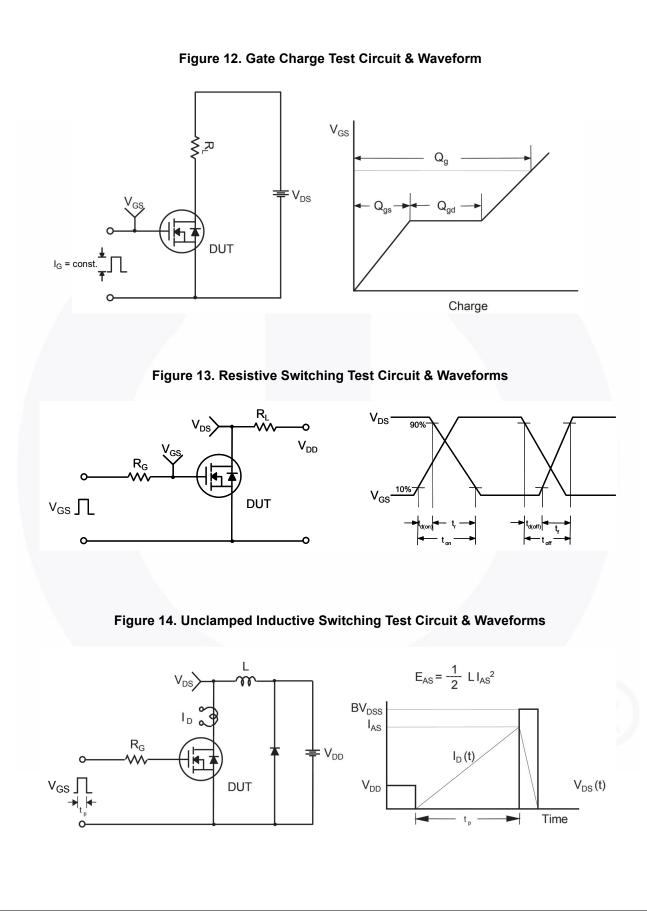
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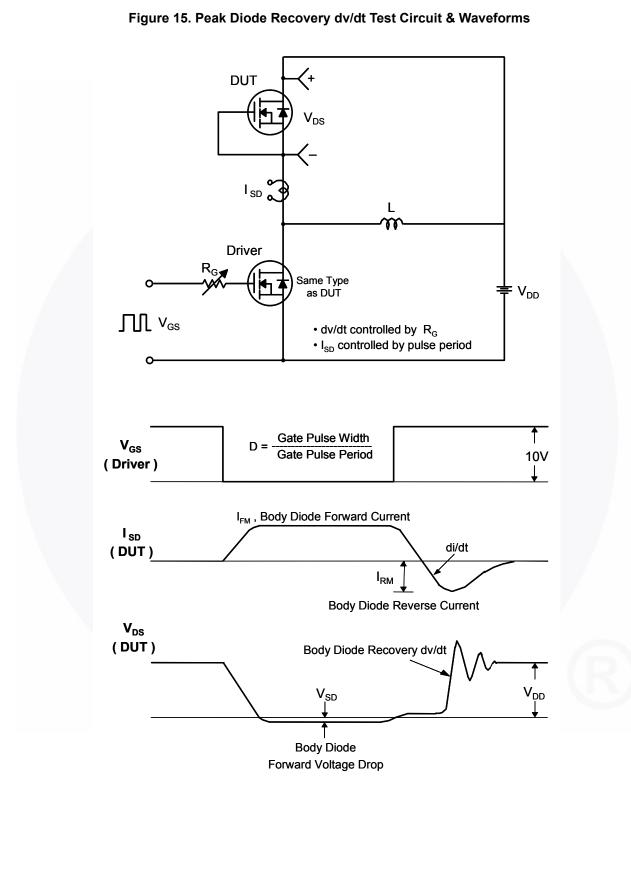
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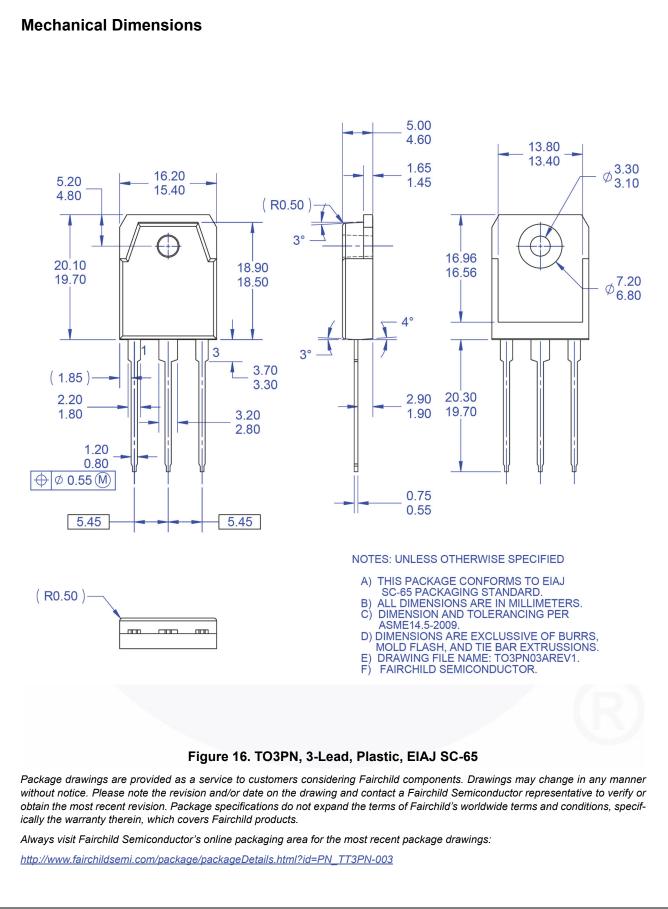
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